PCN	Num				22121							CN Da		December 16, 2022
Title	:		lification c MX as ado										probe	e (EWS) site and
Cust	tomer	Cont	act:		<u>PCN</u>	Man	<u>ager</u>			Dept	t:		Qual	ity Services
Prop	osed	1 <sup>st</sup> Sh	nip Date:	June	16,	2023		Sample Requests accepted until:  Jan 16, 2023*						
*Sar	mple re	equest	s receive	d aft	er Jar	า 16,	2023	will not	be supp	orted				
	nge Ty	_												
		mbly S					Desig				<u></u>			np Site
			rocess			부		Sheet			ᆜ			np Material
			<u> </u>	L:				<u>number</u>	change					np Process
			Specifica ipping/Lal				Test	Sice Process			$\frac{\boxtimes}{\boxtimes}$		r Fab	Materials
	racki	ily/311	прриту/ сат	Jeili	iy	Т	Test	riocess			Ħ			Process
							PC	N Det	ails		_	ware		110000
Desc	criptio	n of (	Change:											
				sed	to ann	oun	ce the	Qualific	ation of	new F	ab	site (R	FAB),	CD-PR as
														lected devices
liste	d in "P	roduct	t Affected'	sec	ction.	Mate	erial di	fference	s are as	follov	vs:			
		С	urrent Fa	ıb S	ite					N	ew	Fab S	ite	
Cu	rrent	Fab	Proce	SS		Wa	fer	Ne	w Fab		Pro	ocess		Wafer
	Site					Dian	neter		Site					Diameter
	MFAE	3	ABCE	06		200	mm			ΑE	3CD6		300 mm	
					Curre	ent:			Ne	w:				
Prol	be Site	e (EWS	S) Ma	ine	Fab (I	MFA	В)	TI C	hengdu	(CD-	PR)			
	erial C up 1 D		ences:											
diot	ם ב קו	CVICE	3.		ASI	ESH		FN	1X					
		Wire	type		1.0 r				nil Cu					
	Мо	old Co	mpound		EN20	0050	)9	421	L880					
	Мо	unt Co	ompound		EY10	0006	53	4147	7858					
	P	<u>in 1 n</u>	narking		D	ot		Din	ıple					
						.,								
	covera son fo		nsertions,	con	aitions	5 WII	rema	in consi	stent wi	tn curi	rent	testin	g. <u> </u>	
Cont	inuity	of Sup	oply											
Anti	cipate	d im	pact on F	orm	, Fit,	Fun	ction,	Qualit	y or Re	lia bili	ty (	positi	ve / ı	negative):
None	9													
Cha	nges t	o pro	duct ide	ntifi	catio	n re	sulting	g from	this PC	N:				
Cur	rent													
_	p Site		Chip Site	Or	iain (2	20L)	Chi	ip Site (	Country	Code	(211	) (	hip Sil	te City
l	NEFAE	3	CUA		ے) ر	,	US	•	,		·	-	•	Portland
[ [17]								, <u>, , , , , , , , , , , , , , , , , , </u>					outii f	orciaria
Nev	w Fab	Site												
	o Site		Chip Site	Or	iain (2	OL)	Chi	p Site Country Code (21L)				) (	hip Sit	te City
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	NAD KED USA							• •				I IX	icriaru	5511

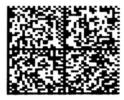
Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
ASESH	ASH	CHN	Shanghai
TI Mexico	MEX	MEX	Aguascalientes

Sample product shipping label (not actual product label)



5A

LBL:



(1P) SN74LS07NSR TKY(1T) 7523483S12 (21L) CCO:USA (20L) CSO: SHE (22L) ASO: MLA (23L) ACO. MYS

## Group 1 Product Affected (Wafer Fab, Probe site, Assembly & Test site):

UCC27282QDDAQ1 UCC27282QDDARQ1

## **Group 2 Product Affected (Wafer Fab site, Probe site only):**

UCC27282QDRCRQ1 UCC27282QDRCTQ1

# **Group 1 Qualification Report**

Approve Date 04-Nov-2022

### Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### **Product Attributes**

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:	QBS Reference:	QBS Reference:
Attributes	UCC27282QDDAQ1	TCAN1042HVDRQ1	TCAN1051VDRQ1	LM5141QRGERQ1	UCC27282QDQ1	LM5169FQDDARQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 150	-40 to 125	-40 to 125	-40 to 125	-40 to 150	-40 to 125
Product Function	Power Management	Interface	Interface	Power Management	Power Management	Power Management
Wafer Fab Supplier	RFAB	MH8	мнв	RFAB	RFAB	RFAB
Assembly Site	FMX	FMX	FMX	UTL1	FMX	FMX
Package Group	SOIC	SOIC	SOIC	QFN	SOIC	SOIC
Package Designator	DDA	D	D	RGE	D	DDA
Pin Count	8	8	8	24	8	8

QBS: Qual By Similarity

Qual Device UCC27282QDDAQ1 is qualified at MSL2 260C

#### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#		Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC27282QDDAQ1	QBS Reference: TCAN1042HVDRQ1			QBS Reference: UCC27282QDQ1	
Test Group	A - Acce	lerated Environ	nment St	ress Te	sts								
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-	No Fails	No Fails	-	-	-

PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	1 Step	No Fails			-	No Fails	No Fails
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	264 Hours	-	-				3/224/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	2/154/0	1/77/0		1/77/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours		2/154/0	1/77/0		1/77/0	
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	110C/85%RH	264 Hours		-				3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	2/154/0	1/77/0		1/77/0	3/210/0
TC-BP	A4	MIL-STD883	1	5	Post Temp	_		1/5/0		_			1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	Cycle Bond Pull High Temperature Storage Life	150C	1000 Hours					1/77/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High	175C	500 Hours		2/90/0	1/45/0			3/135/0
Test Group B	- Accel	erated Lifetime	Simulati	on Test									
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	-	-	-	3/231/0	-	-
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	1000 Hours	-	-	-	-	3/231/0	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours			- :	3/2400/0		-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	150C	48 Hours	-	-	-		1/800/0	-
Test Group C	- Packa	ige Assembly I	ntegrity 1	lests .									
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires		2/60/0	1/30/0		3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	2/60/0	1/30/0	-	3/90/0	3/90/0
SD	СЗ	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage						1/15/0	
SD	СЗ	JEDEC JESD22-		15	PB-Free Solderability	>95% Lead Coverage						1/15/0	1/15/0
		B102	1									1/15/0	1/13/0
PD	C4			10	Physical Dimensions	Cpk>1.67	-	1/10/0	2/20/0	1/10/0		3/30/0	3/30/0
		JEDEC JESD22- B100 and B108	1	10	Physical			1/10/0	2/20/0	1/10/0			
Test Group D		JEDEC JESD22- B100 and	1	10	Physical		-	1/10/0  Completed Per Process Technology Requirements	2/20/0  Completed Per Process Technology Requirements	Completed Per Process Technology	- Completed Per Process Technology Requirements	3/30/0  Completed Per Process Technology	
Test Group D	) - Die Fi	JEDEC JESD22- B100 and B108  abrication Relia	1	10	Physical Dimensions  Electromigration  Time Dependent Dependent Dielectric			Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Process	3/30/0  Completed Per Process	3/30/0  Completed Per Process Technology
Test Group D  EM  TDDB	Die Fi	B102  JEDEC JESD22- B100 and B108  abrication Relia	1	10	Physical Dimensions  Electromigration  Time Dependent			Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements  Completed Per Process Technology
Test Group D  EM  TDDB	D1	B102 JEDEC JESDE2- B100 and B108  abrication Relia JESD61  JESD61	1	10	Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier	Cpl>1.67	-	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements  Completed Per Process Technology	Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Completed Per Process Technology	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology Requirements
Test Group D EM TDDB HCI NBTI	D1 D2 D3	B102 JEDEC JESDE2- B100 and B108  abrication Relia JESD61  JESD61	1	10	Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection	Cpl>1.67	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology	Completed Per Process Technology Requirements	Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology Technology Technology Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements
Test Group D EM TDDB HCI NBTI	D1 D2 D3 D4 D5	B102 JEDEC JESDE2- B100 and B108  abrication Relia JESD61  JESD61	1 1	10	Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability	Cpl>1.67		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Process Technology Requirements Completed Per Process Technology Technology Technology Technology Technology Technology Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements
Test Group D  EM  TDDB  HCI  NBTI  SM  Test Group E	D1 D2 D3 D4 D5	B102 JEDEC JESDE2- B100 and B108  abrication Relia JESD61  JESD60 & 28	1 1	10	Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability	Cpl>1.67	2000 Volts	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Process Technology Requirements Completed Per Process Technology Technology Technology Technology Technology Technology Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements
Test Group D  EM  TDDB  HCI  NBTI  SM  Test Group E	D1 D2 D3 D4 D5 E-Electric	B102 JEDEC JESD22- B100 and B108  abrication Relia JESD61  JESD61  JESD60 & 28	1 1	10 10	Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration	Cpl>1.67		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process  Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Process Technology Requirements Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Requirements Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements
Test Group D  EM  TDDB  HCI  NBTI  SM  Test Group E  ESD  ESD	D1 D2 D3 D4 D5 EEectr	B102 JEDEC JESDC2 B100 and B108  abrication Relia JESD61  JESD60 & 28	1  in Tests  1  1		Physical Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration	Cpl>1.67	Volts 500	Completed Per Process Technology Requirements  - Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements -	Process Technology Requirements  Completed Per Process Technology Requirements  Lompleted Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV:150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL. ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

[1]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D (attached to eQDB) attributed these to board issues andwere discounted as not related to the fab change.

[2]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D

(attached to eQDB) attributed these to board issues andwere discounted as not related to the fab change.

[3]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D (attached to eQDB) attributed these to board issues andwere discounted as not related to the fab change.

[4]-EOS. Discounted

## **Group 2 Qualification Report**

Approve Date 04-Nov-2022

### Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### **Product Attributes**

Attributes	Qual Device: UCC27282QDRCTQ1	Qual Device: UCC27284DRCT	• • • • • • • • • • • • • • • • • • • •	Qual Device: UCC27282DRCT	*		QBS Reference: UCC27282QDQ1	QBS Reference: UCC27284QDQ1	QBS Reference: UCC27289D	QBS Reference: CAXC8T245QRHLRQ1
Automotive Grade Level	Grade 1	-			Grade 1	Grade 1	Grade 1	Grade 1		Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 150	-40 to 150	-40 to 125	-40 to 125
Product Function	Power Management	-	-		Power Management	Power Management	Power Management	Power Management		Signal Chain
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	мн8
Assembly Site	CDAT	CDAT	CDAT	CDAT	CDAT	UTL1	FMX	FMX	FMX	CDAT
Package Group	QFN	QFN	QFN	QFN	-	QFN	SOIC	SOIC	SOIC	QFN
Package Designator	DRC	DRC	DRC	DRC	DRC	RGE	D	D	D	RHL
Pin Count	10	10	10	10	10	24	8	8	8	24

QBS: Qual By Similarity

Qual Device UCC27282QDRCTQ1 is qualified at MSL2 260C

Qual Device UCC27284 DRCT is qualified at MSL2 260C

Qual Device UCC27289 DRCT is qualified at MSL2 260C

Qual Device UCC27282 DRCT is qualified at MSL1 260C

### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре		#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC27282QDRCTQ1	Qual Device: UCC27284DRCT	Qual Device: UCC27289DRCT	Qual Device: UCC27282DRCT	QBS Reference: BQ25171QWDRCRQ1	QBS Reference: UCC27282QDQ1	
Test G	Group /	A - Acce	lerated Enviror	nment St	ress Te:	its									
PC		A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-	-		-		-	
PC		A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	1 Step	1/0/0	-		-	3/0/0	3/0/0	

HAST	A2	JEDEC JESD22- A110	3	77	Temperature Humidity Bias	85C/85%RH	1000 Hours	-				-			-
ACAUHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-				-		1/77/0	
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0				3/231/0		3/231/0	
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	-				1/45/0			-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours					3/135/0		1/77/0	-
Test Group I	B - Acce	lerated Lifetim	e Simula	tion Tes	ts										
HTOL	81	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours					-	3/231/0		-
HTOL	81	JEDEC JESD22- A108	1	77	Life Test	150C	1000 Hours	-				-		3/231/0	-
ELFR	82	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours					-	3/2400/0		
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	150C	48 Hours							1/800/0	-
Test Group	C - Paci	kage Assembly	Integrity	Tests		-	-			3 33					
wes	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.57	Wires	1/30/0	ė.	•	•	3/15/0	*		•
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	*	E		3/15/0			
SD	СЗ	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	•			•		1/15/0	• :		
SD	СЗ	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage						1/15/0	•		
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpic-1.67		1/10/0				3/30/0			
Test Group	D - Die F	abrication Relia	ability Te	sts							20		50		II
ЕМ	D1	JESD61	*		Electromigration		*)	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed I Process Technology Requiremen
тров	D2	JESD35	•		Time Dependent Dielectric Breakdown		8	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed I Process Technology Requirement
HCI	D3	JESD60 &	20	-	Hot Carrier	-		Completed Per	Completed Per	Completed Per	Completed Per	Completed Per	Completed Per	Completed Per	Completed i
		28			Injection			Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirement
NBTI	D4				Negative Bias Temperature Instability		\$	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed I Process Technology Requiremen
SM	D5				Stress Migration			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed F Process Technology Requiremen
Test Group	E - Elec	trical Verificatio	n Tests												
ESD	E2	AEC Q100- 002	1	3	ESD HBM		2000 Volts	1/3/0						1/3/0	1/3/0
ESO	E3	AEC Q100- 011	1	3	ESD CDM		500 Volts	1/3/0						1/3/0	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004		160						1/6/0	1/6/0
ED	ES	AEC Q100-	3	30	Electrical Distributions	Cpk>1.67 Room, hot,	2	1/30/0		i i				3/90/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Am bient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40C to +150C

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

[1]-Fab Defect. Corrective actions implemented

QEM-EVAL-2009-00457

[2]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D (attached to eQDB) attributed these to board issues and were discounted as not related to the fab change.

[3]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D (attached to eQDB) attributed these to board issues andwere discounted as not related to the fab change.

[4]-6 fails across 3 lots (as well as 6 fails on control material) were attributed to electrically induced physical damage. Extensive FA and 8D (attached to eQDB) attributed these to board issues and were discounted as not related to the fab change. [5]-Discounted. QEM-EVAL-1710-00385

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN www admin team@list.ti.com

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